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**NTE4501**  
**Integrated Circuit**  
**CMOS, Dual 4-Input NAND Gate,**  
**2-Input NOR/OR Gate,**  
**8-Input AND/NAND Gate**

**Description:**

The NTE4501 is a “triple gate” device in a 16-Lead DIP type package constructed with MOS P-Channel and N-Channel enhancement mode devices in a single monolithic structure. These complementary MOS logic gates find primary use where low power dissipation and/or high noise immunity is desired.

**Features:**

- Quiescent Current = 0.5nA/package Typ at 5Vdc
- Noise Immunity = 45% of  $V_{DD}$  Typ
- Diode Protection on All Inputs
- Supply Voltage Range: 3Vdc to 18Vdc
- Single Supply Operation – Positive or Negative
- High Fanout > 50
- Logic Swing Independent of fanout
- Capable of Driving Two Low-Power TTL Loads, One Low-Power Schottky TTL Load or Two HTL Loads Over the Rated Temperature Range

**Absolute Maximum Ratings:** (Voltages referenced to  $V_{SS}$ , Note 1)

DC Supply Voltage, $V_{DD}$ .....	-0.5 to +18.0V
Input Voltage (All Inputs), $V_{in}$ .....	-0.5 to $V_{DD}$ to +0.5V
DC Current Drain (Per Pin), I .....	10mA
Operating Temperature Range, $T_A$ .....	-55° to +125°C
Storage Temperature Range, $T_{stg}$ .....	-65° to +150°C

Note 1. Maximum Ratings are those values beyond which damage to the device may occur.

## Electrical Characteristics:

Parameter	Symbol	V <sub>DD</sub> Vdc	-55°C		+25°C			+125°C		Unit	
			Min	Max	Min	Typ	Max	Min	Max		
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0  "0" Level  "1" Level V <sub>in</sub> = 0 or V <sub>DD</sub>	V <sub>OL</sub>	5.0	-	0.05	-	0	0.05	-	0.05	Vdc	
		10	-	0.05	-	0	0.05	-	0.05	Vdc	
		15	-	0.05	-	0	0.05	-	0.05	Vdc	
	V <sub>OH</sub>	5.0	4.95	-	4.95	5.0	-	4.95	-	Vdc	
		10	9.95	-	9.95	10	-	9.95	-	Vdc	
		15	14.95	-	14.95	15	-	14.95	-	Vdc	
Input Voltage (Note 2) (V <sub>O</sub> = 3.6 or 1.4Vdc) (V <sub>O</sub> = 7.2 or 2.8Vdc) (V <sub>O</sub> = 11.5 or 3.5Vdc)  "0" Level  "1" Level (V <sub>O</sub> = 1.4 or 3.6Vdc) (V <sub>O</sub> = 12.8 or 7.2Vdc) (V <sub>O</sub> = 3.5 or 11.5Vdc)	V <sub>IL</sub>	5.0	-	1.5	-	2.25	1.5	-	1.4	Vdc	
		10	-	3.0	-	4.50	3.0	-	2.9	Vdc	
		15	-	3.75	-	6.75	3.75	-	3.6	Vdc	
	V <sub>IH</sub>	5.0	3.6	-	3.5	2.75	-	3.5	-	Vdc	
		10	7.1	-	7.0	5.50	-	7.0	-	Vdc	
		15	11.4	-	11.25	8.25	-	11.0	-	Vdc	
Output Drive Current (V <sub>OH</sub> = 2.5Vdc) (V <sub>OH</sub> = 4.6Vdc) (V <sub>OH</sub> = 9.5Vdc) (V <sub>OH</sub> = 13.5Vdc) (V <sub>OH</sub> = 2.5Vdc) (V <sub>OH</sub> = 4.6Vdc) (V <sub>OH</sub> = 9.5Vdc) (V <sub>OH</sub> = 13.5Vdc) (V <sub>OH</sub> = 2.5Vdc) (V <sub>OH</sub> = 4.6Vdc) (V <sub>OH</sub> = 9.5Vdc) (V <sub>OH</sub> = 13.5Vdc) (V <sub>OL</sub> = 0.4Vdc) (V <sub>OL</sub> = 0.5Vdc) (V <sub>OL</sub> = 1.5Vdc) (V <sub>OL</sub> = 0.4Vdc) (V <sub>OL</sub> = 0.5Vdc) (V <sub>OL</sub> = 1.5Vdc) (V <sub>OL</sub> = 0.4Vdc) (V <sub>OL</sub> = 0.5Vdc) (V <sub>OL</sub> = 1.5Vdc)	Source  NAND  NOR  NOR  Inverter	I <sub>OH</sub>	5.0	-1.2	-	-1.0	-1.7	-	-0.7	-	mAdc
			5.0	-0.25	-	-0.2	-0.36	-	-0.14	-	mAdc
			10	-0.62	-	-0.5	-0.9	-	-0.35	-	mAdc
			15	-1.8	-	-1.5	-3.5	-	-1.1	-	mAdc
			5.0	-2.1	-	-1.75	-3.0	-	-1.22	-	mAdc
			5.0	-0.42	-	-0.36	-0.63	-	-0.24	-	mAdc
			10	-1.06	-	-0.88	-1.58	-	-0.62	-	mAdc
			15	-3.1	-	-3.0	-5.1	-	-2.1	-	mAdc
			5.0	-3.6	-	-1.75	-3.0	-	-1.22	-	mAdc
	Sink NAND  NOR  NOR  Inverter	I <sub>OL</sub>	5.0	0.64	-	0.51	0.88	-	0.36	-	mAdc
			10	1.6	-	1.3	2.25	-	0.9	-	mAdc
			15	4.2	-	3.4	8.8	-	2.4	-	mAdc
			5.0	0.92	-	0.77	1.32	-	0.54	-	mAdc
			10	2.34	-	1.95	3.37	-	1.36	-	mAdc
			15	6.12	-	5.1	13.2	-	3.57	-	mAdc
			5.0	1.54	-	1.28	2.2	-	0.9	-	mAdc
			10	3.9	-	3.25	5.63	-	2.27	-	mAdc
			15	10.2	-	8.5	22	-	5.95	-	mAdc

Note 2. Noise immunity specified for worse case input combination.

Note 3. The formulas given are for the typical characteristics only at +25°C.

Note 4. To calculate total supply current at loads other than 50pF:

$$I_T(C_L) = I_T(50\text{pF}) + 4 \times 10^{-3}(C_L - 50) V_{DD}/f$$

where: I<sub>T</sub> is in μA (per package), C<sub>L</sub> in pF, V<sub>DD</sub> in Vdc, f in kHz is input frequency.

### Electrical Characteristics (Cont'd):

Parameter	Symbol	V <sub>DD</sub> Vdc	-55°C		+25°C			+125°C		Unit
			Min	Max	Min	Typ	Max	Min	Max	
Input Current	I <sub>in</sub>	15	-	±0.1	-	±0.00001	±0.1	-	±0.1	µA <sub>dc</sub>
Input Capacitance (V <sub>IN</sub> = 0)	C <sub>in</sub>	-	-	-	-	5.0	7.5	-	-	pF
Quiescent Current (Per Package)	I <sub>DD</sub>	5.0	-	0.05	-	0.0005	0.5	-	1.5	µA <sub>dc</sub>
		10	-	0.10	-	0.0010	0.10	-	3.0	µA <sub>dc</sub>
		15	-	0.20	-	0.0015	0.20	-	6.0	µA <sub>dc</sub>
Total Supply Current (Dynamic plus Quiescent, Per Package, C <sub>L</sub> = 50pF on all outputs, all buffers switching, Note 3, Note 4)	I <sub>T</sub>	5.0	I <sub>T</sub> = (1.2µA/kHz) f + I <sub>DD</sub>							µA <sub>dc</sub>
		10	I <sub>T</sub> = (2.4µA/kHz) f + I <sub>DD</sub>							µA <sub>dc</sub>
		15	I <sub>T</sub> = (3.6µA/kHz) f + I <sub>DD</sub>							µA <sub>dc</sub>

Note 2. Noise immunity specified for worse case input combination.

Note 3. The formulas given are for the typical characteristics only at +25°C.

Note 4. To calculate total supply current at loads other than 50pF:

$$I_T(C_L) = I_T(50\text{pF}) + 4 \times 10^{-3}(C_L - 50) V_{DD}/f$$

where: I<sub>T</sub> is in µA (per package), C<sub>L</sub> in pF, V<sub>DD</sub> in Vdc, f in kHz is input frequency.

### Switching Characteristics: (C<sub>L</sub> = 50pF, T<sub>A</sub> = +25°C, Note 2, Note 3)

Parameter	Symbol	V <sub>DD</sub> Vdc	Min	Typ	Max	Unit
Output Rise Time t <sub>TLH</sub> = (3.0ns/pf) C <sub>L</sub> + 30ns t <sub>TLH</sub> = (1.5ns/pf) C <sub>L</sub> + 15ns t <sub>TLH</sub> = (1.1ns/pf) C <sub>L</sub> + 10ns	t <sub>TLH</sub>	5.0	-	180	360	ns
		10	-	90	180	ns
		15	-	65	130	ns
Output Fall Time t <sub>THL</sub> = (1.5ns/pf) C <sub>L</sub> + 25ns t <sub>THL</sub> = (0.75ns/pf) C <sub>L</sub> + 12.5ns t <sub>THL</sub> = (0.55ns/pf) C <sub>L</sub> + 9.5ns	t <sub>THL</sub>	5.0	-	100	200	ns
		10	-	50	100	ns
		15	-	40	80	ns
Output Rise Time t <sub>TLH</sub> = (1.35ns/pf) C <sub>L</sub> + 32.5ns t <sub>TLH</sub> = (0.60ns/pf) C <sub>L</sub> + 20ns t <sub>TLH</sub> = (0.40ns/pf) C <sub>L</sub> + 17ns	t <sub>TLH</sub>	5.0	-	100	200	ns
		10	-	50	100	ns
		15	-	40	80	ns
Output Fall Time t <sub>THL</sub> = (0.67ns/pf) C <sub>L</sub> + 26.5ns t <sub>THL</sub> = (0.45ns/pf) C <sub>L</sub> + 17.5ns t <sub>THL</sub> = (0.37ns/pf) C <sub>L</sub> + 11.5ns	t <sub>THL</sub>	5.0	-	60	120	ns
		10	-	40	80	ns
		15	-	30	60	ns

Note 2. Data labeled "Typ" is not to be used for design purposes but is intended as an indication of the device's potential performance.

Note 3. The formulas given are for the typical characteristics only at +25°C.

**Switching Characteristics (Cont'd):** ( $C_L = 50\text{pF}$ ,  $T_A = +25^\circ\text{C}$ , Note 2, Note 3)

Parameter	Symbol	$V_{DD}$ Vdc	Min	Typ	Max	Unit	
Propagation Delay Time $t_{PLH}, t_{PHL} = (1.7\text{ns/pf}) C_L + 45\text{ns}$ $t_{PLH}, t_{PHL} = (0.66\text{ns/pf}) C_L + 37\text{ns}$ $t_{PLH}, t_{PHL} = (0.5\text{ns/pf}) C_L + 25\text{ns}$ $t_{PLH}, t_{PHL} = (1.7\text{ns/pf}) C_L + 30\text{ns}$ $t_{PLH}, t_{PHL} = (0.66\text{ns/pf}) C_L + 32\text{ns}$ $t_{PLH}, t_{PHL} = (0.5\text{ns/pf}) C_L + 20\text{ns}$ $t_{PLH}, t_{PHL} = (1.7\text{ns/pf}) C_L + 45\text{ns}$ $t_{PLH}, t_{PHL} = (0.66\text{ns/pf}) C_L + 37\text{ns}$ $t_{PLH}, t_{PHL} = (0.5\text{ns/pf}) C_L + 25\text{ns}$	NAND	$t_{PLH}, t_{PHL}$	5.0	-	130	260	ns
			10	-	70	140	ns
			15	-	50	100	ns
	NOR	$t_{PLH}, t_{PHL}$	5.0	-	115	230	ns
			10	-	65	130	ns
			15	-	45	90	ns
	NOR-Inverter	$t_{PLH}, t_{PHL}$	5.0	-	130	260	ns
			10	-	70	140	ns
			15	-	50	100	ns

Note 2. Data labeled "Typ" is not to be used for design purposes but is intended as an indication of the device's potential performance.

Note 3. The formulas given are for the typical characteristics only at  $+25^\circ\text{C}$ .



